

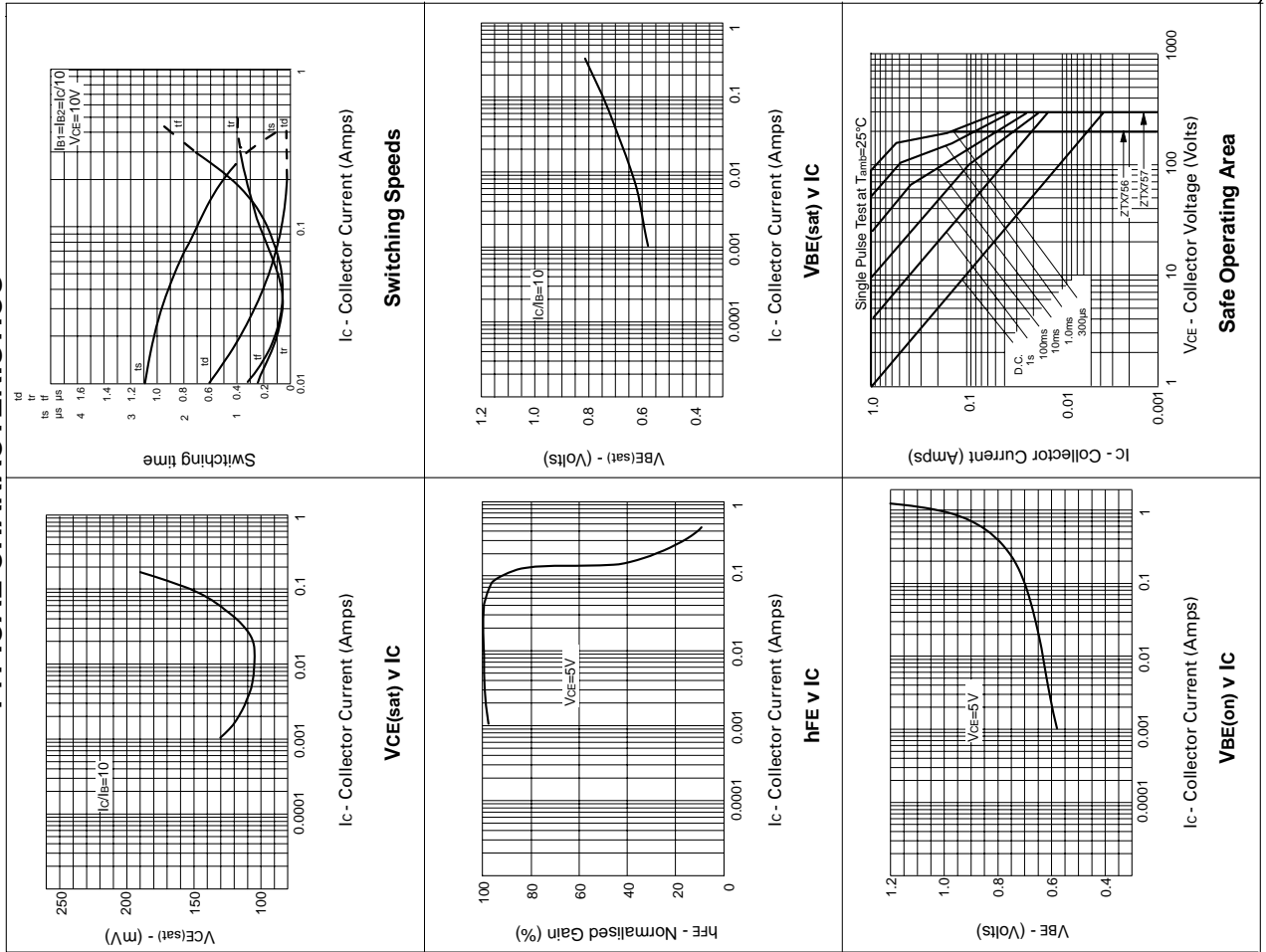
**ZTX756
ZTX757**

**PNP SILICON PLANAR MEDIUM POWER
HIGH VOLTAGE TRANSISTORS**

ISSUE 2 - JULY 94

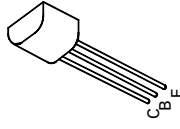
**ZTX756
ZTX757**

TYPICAL CHARACTERISTICS



FEATURES

- * 300 Volt V_{CEO}
- * 0.5 Amp continuous current
- * $P_{tot}=1$ Watt



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX756	ZTX757	UNIT
Collector-Base Voltage	V_{CBO}	-200	-300	V
Collector-Emitter Voltage	V_{CEO}	-200	-300	V
Emitter-Base Voltage	V_{EBO}	-5	-5	V
Peak Pulse Current	I_{CM}	-1	-1	A
Continuous Collector Current	I_C	-0.5	-0.5	A
Power Dissipation at $T_{amb}=25^\circ C$	P_{tot}	1	1	W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +200		$^\circ C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ unless otherwise stated).

PARAMETER	SYMBOL	ZTX756		ZTX757		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-200	-300			V	$I_C=-100\mu A, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-200	-300			V	$I_C=-10mA, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-5			V	$I_E=-100\mu A, I_C=0$
Collector Cut-Off Current	I_{CBO}		-100		-100	nA	$V_{CB}=-160V, I_E=0$ $V_{CB}=-200V, I_E=0$
Emitter Cut-Off Current	I_{EBO}		-100		-100	nA	$V_{EB}=-3V, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.5		-0.5	V	$I_C=-100mA, I_B=-10mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.0		-1.0	V	$I_C=-100mA, I_B=-10mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-1.0		-1.0	V	$I_C=-100mA, V_{CE}=-5V^*$
Static Forward Current Transfer Ratio	h_{FE}	50 40	50 40				$I_C=-100mA, V_{CE}=-5V^*$ $I_C=-10mA, V_{CE}=-5V^*$
Transition Frequency	f_T	30	30			MHz	$I_C=-10mA, V_{CE}=-20V$ $f=20MHz$
Output Capacitance	C_{obo}	20	20		20	pF	$V_{CB}=-20V, f=1MHz$

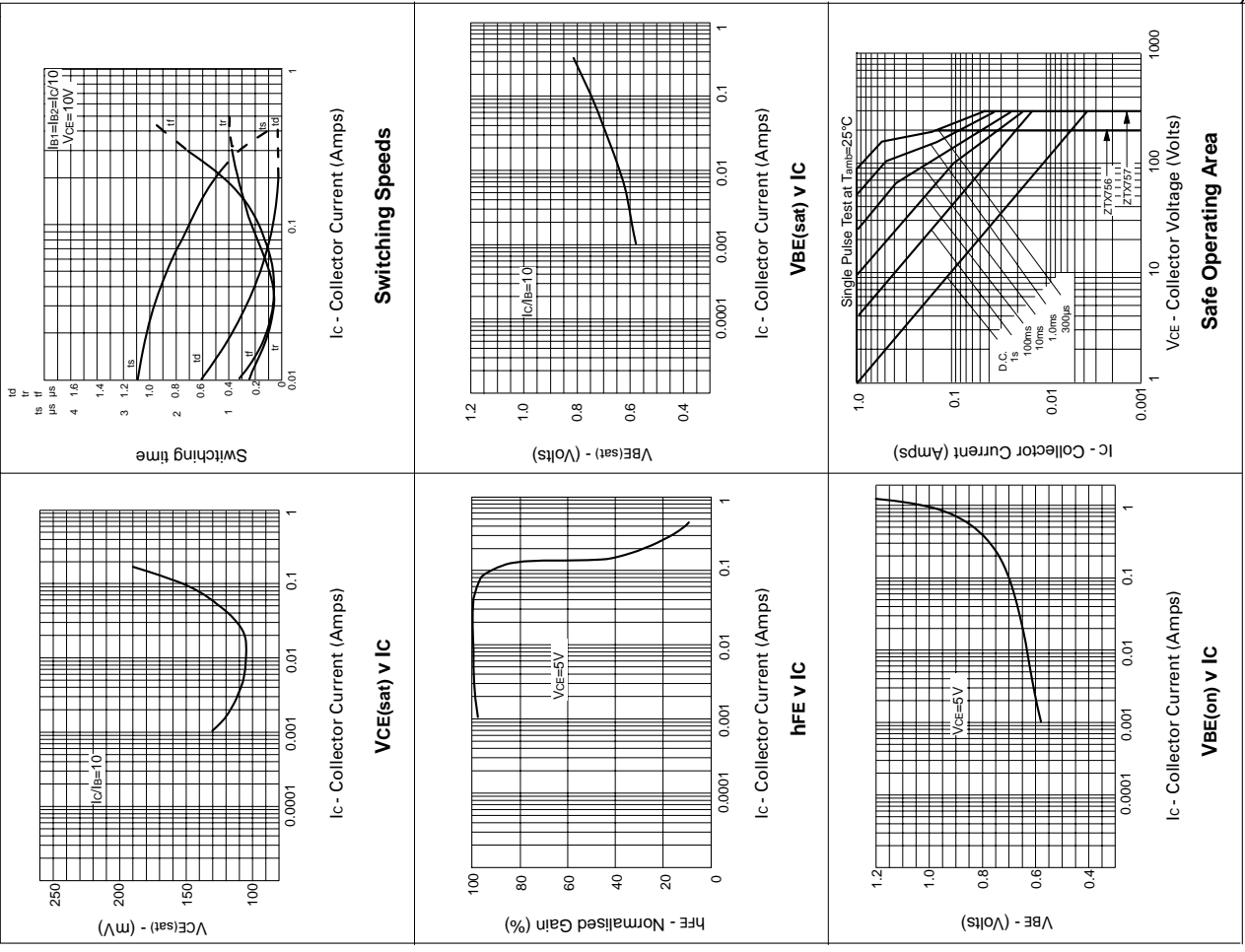
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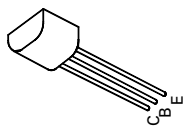
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Power Dissipation at $T_{amb}=25^\circ C$	P_{tot}	1	1	W
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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ unless otherwise stated).

PARAMETER	SYMBOL	ZTX756		ZTX757		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-200	-300			V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-200	-300			V	$I_C = -10mA, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-5			V	$I_E = -100\mu A, I_C = 0$
Collector Cut-Off Current	I_{CBO}		-100		-100	nA	$V_{CE} = -160V, I_E = 0$ $V_{CB} = -200V, I_E = 0$
Emitter Cut-Off Current	I_{EBO}		-100		-100	nA	$V_{EB} = -3V, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-0.5	-0.5	-0.5	-0.5	V	$I_C = -100mA, I_B = -10mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-1.0	-1.0	-1.0	-1.0	V	$I_C = -100mA, I_B = -10mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	-1.0	-1.0	-1.0	-1.0	V	$I_C = -100mA, V_{CE} = -5V^*$
Static Forward Current Transfer Ratio	h_{FE}	50 40	50 40				$I_C = -100mA, V_{CE} = -5V^*$ $I_C = -10mA, V_{CE} = -5V^*$
Transition Frequency	f_T	30	30			MHz	$I_C = -10mA, V_{CE} = -20V$ $f = 20MHz$
Output Capacitance	C_{obo}	20	20	20	20	pF	$V_{CB} = -20V, f = 1MHz$